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Power logic 8-bit shift register; open-drain outputsRev. 1 — 20 August 2012Product

Product data sheet

1. General description

The NPIC6C595 is an 8-bit serial-in/serial or parallel-out shift register with a storage register and open-drain outputs. Both the shift and storage register have separate clocks. The device features a serial input (DS) and a serial output (Q7S) to enable cascading and an asynchronous reset input (MR). A LOW on MR resets both the shift register and storage register. Data is shifted on the LOW-to-HIGH transitions of the SHCP input. The data in the shift register is transferred to the storage register on a LOW-to-HIGH transition of the STCP input and to the Q7S output on a LOW-to-HIGH transition of the SHCP input. If both clocks are connected together, the shift register is always one clock pulse ahead of the storage register. Data in the storage register drives the gate of the output extended-drain NMOS transistor whenever the output enable input (OE) is LOW. A HIGH on OE causes the outputs to assume a high-impedance OFF-state. Operation of the OE input does not affect the state of the registers. The open-drain outputs are 33 V/100 mA continuous current extended-drain NMOS transistors designed for use in systems that require moderate load power such as LEDs. Integrated voltage clamps in the outputs provide protection against inductive transients. This feature makes the device suitable for power driver applications such as relay, solenoids and other low-current or medium-voltage loads.

2. Features and benefits

- Specified from –40 °C to +125 °C
- Low R_{DSon}
- Eight Power EDNMOS transistor outputs of 100 mA continuous current
- 250 mA current limit capability
- Output clamping voltage 33 V
- 30 mJ avalanche energy capability
- All registers cleared with single input
- Low power consumption
- ESD protection:
 - HBM JDS-001 Class 2 exceeds 2500 V
 - CDM JESD22-C101E exceeds 1000 V

3. Applications

- LED sign
- Graphic status panel
- Fault status indicator

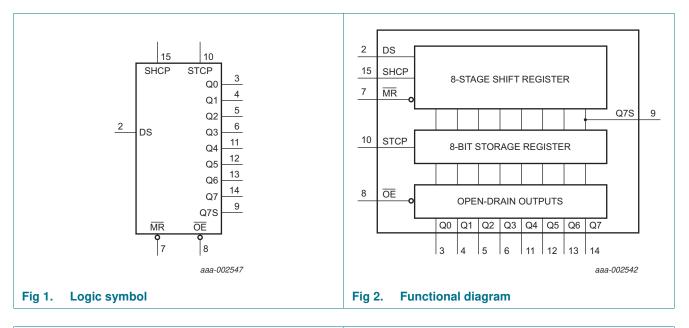


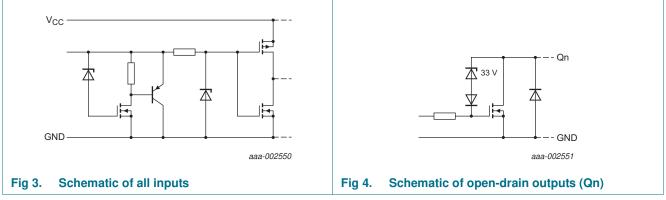
Power logic 8-bit shift register; open-drain outputs

4. Ordering information

Type number	Package	Package						
	Temperature range	Name	Description	Version				
NPIC6C595D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1				
NPIC6C595PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1				
NPIC6C595BQ	–40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body $2.5 \times 3.5 \times 0.85$ mm	SOT763-1				

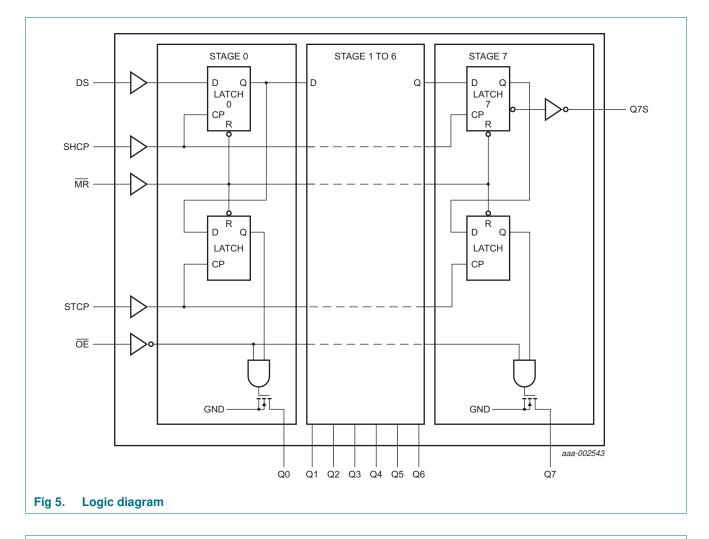
5. Functional diagram

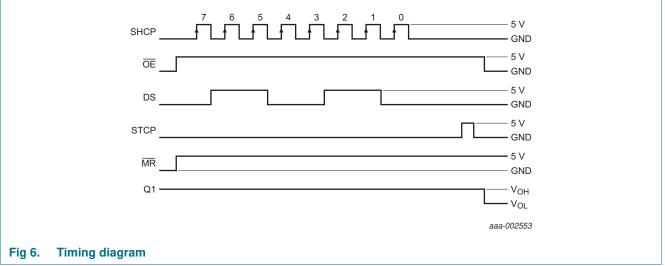




NPIC6C595

Power logic 8-bit shift register; open-drain outputs





Product data sheet

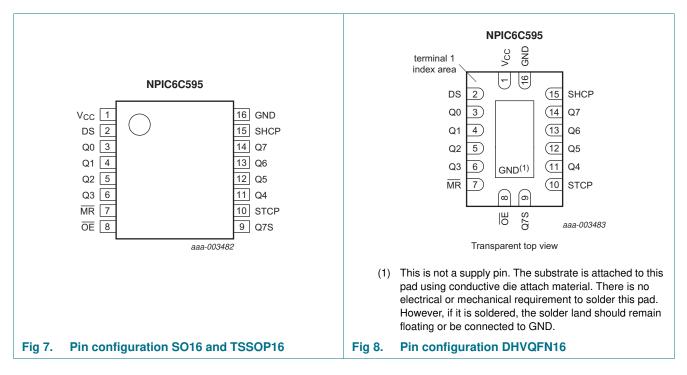
NPIC6C595

3 of 20

Power logic 8-bit shift register; open-drain outputs

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2.Pin description

Symbol	Pin	Description
V _{CC}	1	supply voltage
DS	2	serial data input
Q0, Q1, Q2, Q3, Q4, Q5, Q6, Q7	3, 4, 5, 6, 11, 12, 13, 14	parallel data output (open-drain)
MR	7	master reset (active LOW)
ŌE	8	output enable input (active LOW)
Q7S	9	serial data output
STCP	10	storage register clock input
SHCP	15	shift register clock input
GND	16	ground (0 V)

Power logic 8-bit shift register; open-drain outputs

7. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

				,
Parameter	Conditions	Min	Max	Unit
supply voltage		-0.5	+7.0	V
input voltage		-0.3	+7.0	V
drain-source voltage	power EDNMOS drain-source voltage	<u>[1]</u> -	+33	V
source-drain diode current	continuous	-	250	mA
	pulsed	[2] _	500	mA
drain current	T _{amb} = 25 °C			
	continuous; each output; all outputs on	-	100	mA
	pulsed; each output; all outputs on	[2] _	250	mA
peak drain current	single output; $T_{amb} = 25 \ ^{\circ}C$	[2] _	250	mA
non-repetitive avalanche energy	single pulse; see <u>Figure 9</u>	[3] _	30	mJ
avalanche current	see Figure 9	[3] _	200	mA
storage temperature		-65	+150	°C
total power dissipation	T _{amb} = 25 °C	[4]		
	SO16	-	800	mW
	TSSOP16	-	725	mW
	DHVQFN16	-	1825	mW
	DHVQFN16 T _{amb} = 125 °C	- [4]	1825	mW
		- [4] -	1825 160	mW
	T _{amb} = 125 °C			
	supply voltage input voltage drain-source voltage source-drain diode current drain current peak drain current non-repetitive avalanche energy avalanche current storage temperature	$supply voltage$ input voltage $drain-source voltage$ $source-drain diode current$ $continuous$ $pulsed$ $drain current$ $T_{amb} = 25 ^{\circ}C$ $continuous; each output; all outputs on$ $pulsed; each output; all outputs on$ $peak drain current$ single output; $T_{amb} = 25 ^{\circ}C$ $ron-repetitive avalanche energy$ storage temperature $total power dissipation$ $T_{amb} = 25 ^{\circ}C$ $SO16$	$\begin{aligned} \text{supply voltage} & -0.5 \\ \text{input voltage} & -0.3 \\ \text{drain-source voltage} & \text{power EDNMOS drain-source} & 11 & - \\ \text{voltage} & 11 & - \\ \text{source-drain diode current} & \text{continuous} & - \\ \text{pulsed} & 12 & - \\ \text{pulsed} & 12 & - \\ \text{drain current} & \text{T_{amb}} = 25 \ ^{\circ}\text{C} & 12 & - \\ \text{continuous; each output;} & - \\ \text{all outputs on} & 12 & - \\ \text{pulsed; each output;} & - \\ \text{all outputs on} & 12 & - \\ \text{pulsed; each output;} & 12 & - \\ \text{single output; T_{amb}} = 25 \ ^{\circ}\text{C} & 12 & - \\ \text{non-repetitive avalanche energy} & \text{single pulse; see Figure 9} & 13 & - \\ \text{avalanche current} & \text{see Figure 9} & 13 & - \\ \text{storage temperature} & -65 & 14 & - \\ \text{sonal power dissipation} & \text{T_{amb}} = 25 \ ^{\circ}\text{C} & 14 & - \\ \hline \text{SO16} & - \\ \text{TSSOP16} & - \\ \end{array}$	$\begin{split} \text{supply voltage} & -0.5 & +7.0 \\ \text{input voltage} & -0.3 & +7.0 \\ \text{drain-source voltage} & \text{power EDNMOS drain-source} & 11 & -33 \\ \text{source-drain diode current} & \text{continuous} & -250 \\ \text{pulsed} & 21 & -500 \\ \text{drain current} & & & & & & & & & & & & & & & & & & &$

[1] Each power EDNMOS source is internally connected to GND.

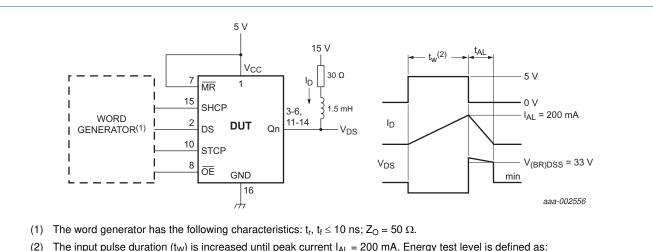
[2] Pulse duration \leq 100 μ s and duty cycle \leq 2 %.

[3] $V_{DS} = 15$ V; starting junction temperature (T_j) = 25 °C; L = 1.5 H; avalanche current (I_{AL}) = 200 mA.

[4] For SO16 packages: above 25 °C the value of P_{tot} derates linearly with 6.4 mW/°C. For TSSOP16 packages: above 25 °C the value of P_{tot} derates linearly with 5.8 mW/°C.

For DHVQFN16 packages: above 25 °C the value of Ptot derates linearly with 14.6 mW/°C.

Power logic 8-bit shift register; open-drain outputs



7.1 Test circuit and waveform

(2) The input pulse duration (t_W) is increased until peak current I_{AL} = 200 mA. Energy test level is defined as: $E_{AS} = I_{AL} \times V_{(BR)DSS} \times t_{AL}/2 = 30$ mJ.

Fig 9. Test circuit and waveform for measuring single-pulse avalanche energy

8. Recommended operating conditions

Table 4. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		4.5	-	5.5	V
VI	input voltage		0	-	5.5	V
I _D	drain current	pulsed drain output current; V _{CC} = 5 V; T _{amb} = 25 °C; all outputs on	[1][2] _	-	250	mA
T _{amb}	ambient temperature		-40	-	+125	°C

[1] Pulse duration \leq 100 μ s and duty cycle \leq 2 %.

[2] This technique should limit $T_i - T_{amb}$ to 10 °C maximum.

9. Static characteristics

Table 5.Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	V _{CC} = 5.0 V; T _{amb} = 25 °C			Unit
			Min	Тур	Max	
V _{IH}	HIGH-level input voltage	$V_{CC} = 4.5 V \text{ to } 5.5 V$	0.85V _{CC}	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 4.5 V \text{ to } 5.5 V$	-	-	0.15V _{CC}	V
V _{OH}	HIGH-level	serial data output Q7S; $V_I = V_{IH}$ or V_{IL}				
	output voltage	$I_O = -20 \ \mu A; \ V_{CC} = 4.5 \ V$	4.4	4.49	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.0	4.2	-	V

Power logic 8-bit shift register; open-drain outputs

Symbol	Parameter	Conditions		V _{CC} =	5.0 V; T _{amb} :	= 25 °C	Unit
				Min	Тур	Max	
V _{OL}	•	serial data output Q7S; $V_I = V_{IH}$ or V_{IL}	l		1 1		
	voltage	$I_{O} = 20 \ \mu A; \ V_{CC} = 4.5 \ V$		-	0.005	0.1	V
		$I_{O} = 4 \text{ mA}; V_{CC} = 4.5 \text{ V}$		-	0.3	0.5	V
IIH	HIGH-level input current	$V_{CC} = 5.5 \text{ V}; \text{V}_{\text{I}} = \text{V}_{CC}$		-	-	1	μA
I _{IL}	LOW-level input current	$V_{CC} = 5.5 \text{ V}; \text{ V}_{I} = 0 \text{ V}$		-	-	-1	μA
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 1 mA		33	37	-	V
V _{SD}	source-drain voltage	diode forward voltage; $I_F = 100 \text{ mA}$		-	0.85	1.2	V
I _{CC}	supply current	logic supply current; $V_{CC} = 5.5 \text{ V}$; $V_I = V_{CC} \text{ or GND}$					
		all outputs off		-	0.004	200	μA
		all outputs on		-	0.006	500	μA
		all outputs off; SHCP = 5 MHz; C_L = 30 pF; see Figure 14 and Figure 16		-	0.75	5	mA
I _{O(nom)}	nominal output current	$V_{DS} = 0.5 \text{ V}; \text{T}_{amb} = 85 ^{\circ}\text{C}; \text{I}_{out} = \text{I}_{D}$	<u>[1][2][3]</u>	-	140	-	mA
I _{DSX}	drain cut-off	$V_{CC} = 5.5 \text{ V}; V_{DS} = 30 \text{ V}$		-	0.002	0.2	μA
	current	V_{CC} = 5.5 V; V_{DS} = 30 V; T_{amb} = 125 $^\circ C$		-	0.15	0.3	μA
R_{DSon}	drain-source	see Figure 17 and Figure 18	[1][2]				
	on-state resistance	$V_{CC} = 4.5 \text{ V}; \text{ I}_{D} = 50 \text{ mA}$		-	3.0	9	Ω
	10010100	V_{CC} = 4.5 V; I_{D} = 50 mA; T_{amb} = 125 °C			5.4	12	Ω
		$V_{CC} = 4.5 \text{ V}; \text{ I}_{D} = 100 \text{ mA}$		-	3.1	10	Ω

Table 5. Static characteristics ... continued

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

[1] This technique should limit $T_j - T_{amb}$ to 10 °C maximum.

[2] These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

[3] Nominal output current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at T_{amb} = 85 °C.

Power logic 8-bit shift register; open-drain outputs

10. Dynamic characteristics

Table 6. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); For test circuit see Figure 14.

Symbol	Parameter	Conditions		$V_{CC} = 5$	5.0 V; T _{amb}	= 25 °C	Unit
				Min	Тур	Max	
t _{PLH}	LOW to HIGH propagation delay	\overline{OE} to Qn; I _D = 75 mA; see <u>Figure 10</u> and <u>Figure 19</u>		-	97	-	ns
t _{PHL}	HIGH to LOW propagation delay	\overline{OE} to Qn; I _D = 75 mA; see <u>Figure 10</u> and Figure 19		-	9	-	ns
t _r	rise time	\overline{OE} to Qn; I _D = 75 mA; see <u>Figure 10</u> and <u>Figure 19</u>		-	60	-	ns
t _f	fall time	\overline{OE} to Qn; I _D = 75 mA; see <u>Figure 10</u> and Figure 19		-	18	-	ns
t _{pd}	propagation delay	SHCP to Q7S; $I_D = 75$ mA; see Figure 11	[1]	-	5	-	ns
f _{max}	maximum frequency	SHCP; I _D = 75 mA; see <u>Figure 11</u>	[2]	-	-	10	MHz
t _{rr}	reverse recovery time	I _F = 100 mA; dl/dt = 10 A/μs; see <u>Figure 13</u>	<u>[3][4]</u>	-	120	-	ns
ta	reverse recovery current rise time	I _F = 100 mA; dl/dt = 10 A/μs; see <u>Figure 13</u>	<u>[3][4]</u>	-	100	-	ns
t _{su}	set-up time	DS to SHCP; see Figure 12		20	-	-	ns
t _h	hold time	DS to SHCP; see Figure 12		20	-	-	ns
tw	pulse width			40	-	-	ns

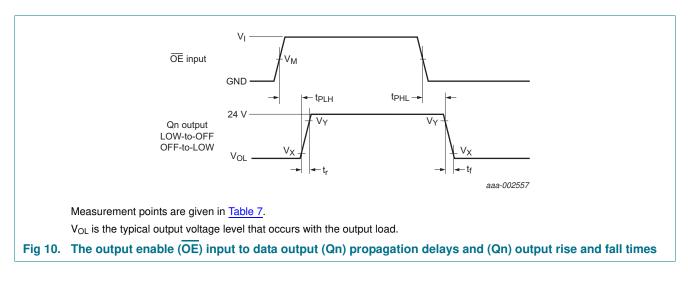
[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] This is the maximum serial clock frequency assuming cascaded operation where serial data is passed from one stage to a second stage. The clock period allows for SHCP → Q7S propagation delay and setup time plus some timing margin.

[3] This technique should limit T_j-T_{amb} to 10 $^\circ C$ maximum.

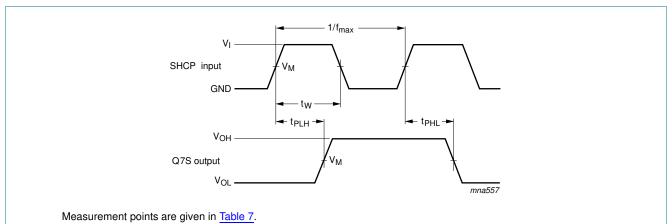
[4] These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

10.1 Test circuits and waveforms



NPIC6C595

Power logic 8-bit shift register; open-drain outputs



 V_{OL} and V_{OH} are the typical output voltage levels that occur with the output load.

Fig 11. The shift clock (SHCP) to serial data output (Q7S) propagation delays, the shift clock pulse width and maximum shift clock frequency

Table 7. Measurement points

Supply voltage	Input	Output		
V _{CC}	V _M	V _M	V _X	V _Y
5 V	0.5V _{CC}	0.5V _{DS}	0.1V _{DS}	0.9V _{DS}

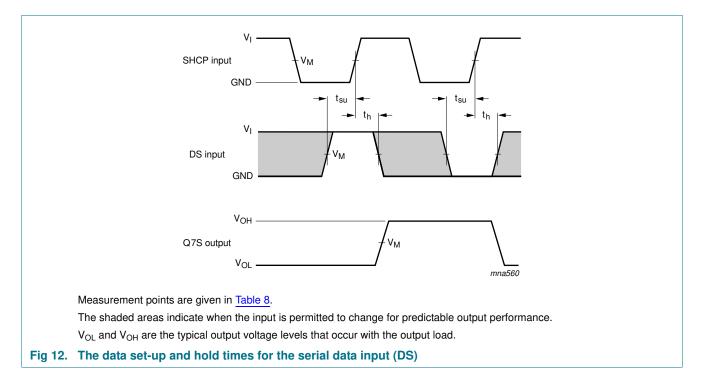


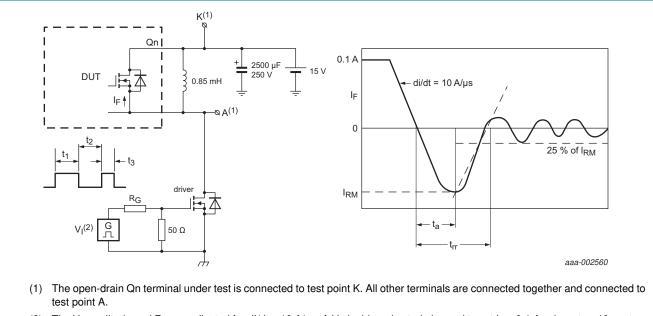
Table 8. Measurement points

Supply voltage	Input	Output
V _{cc}	V _M	V _M
5 V	0.5V _{CC}	0.5V _{CC}

NPI	C6C595	

NPIC6C595

Power logic 8-bit shift register; open-drain outputs



(2) The V₁ amplitude and R_G are adjusted for dI/dt = 10 A/ μ s. A V₁ double-pulse train is used to set I_F = 0.1 A, where t₁ = 10 μ s, t₂ = 7 μ s and t₃ = 3 μ s.

Fig 13. Test circuit and waveform for measuring reverse recovery current

Product data sheet

NPIC6C595

Power logic 8-bit shift register; open-drain outputs

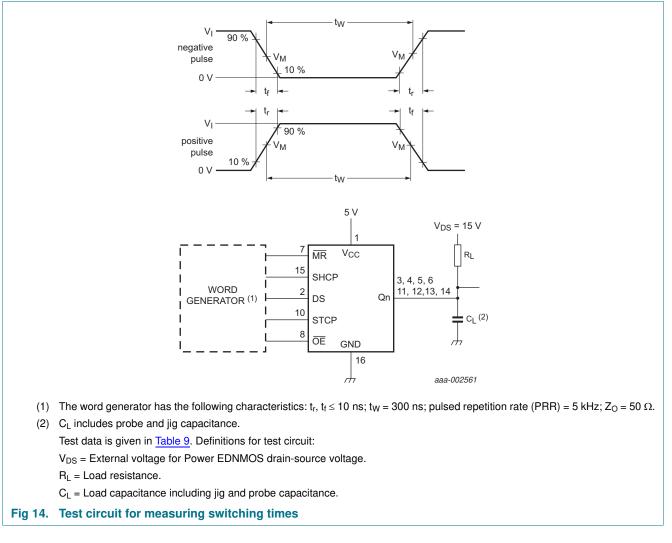
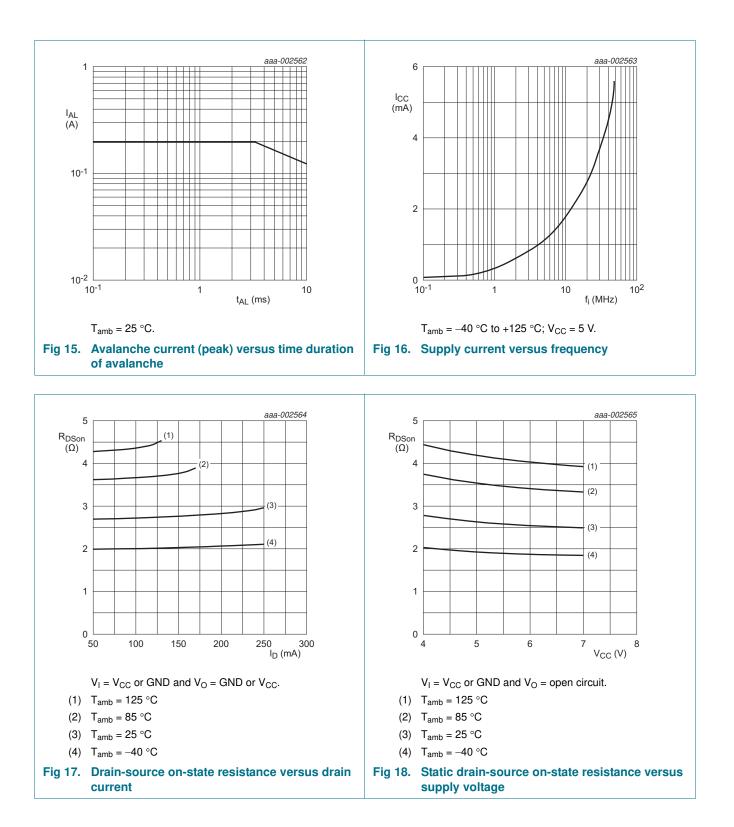


Table 9. Test data

Supply voltage	Input			Load		
	VI	t _r , t _f	V _M	CL	RL	
5 V	5 V	≤ 10 ns	50 %	30 pF	200 Ω	

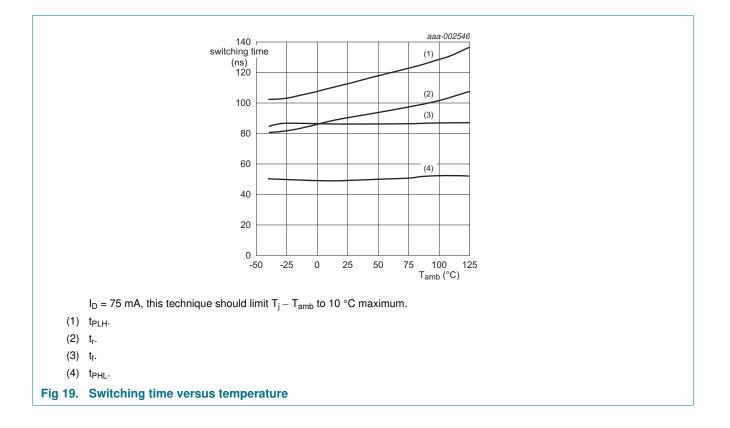
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Power logic 8-bit shift register; open-drain outputs



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Power logic 8-bit shift register; open-drain outputs



NPIC6C595

Power logic 8-bit shift register; open-drain outputs

11. Package outline

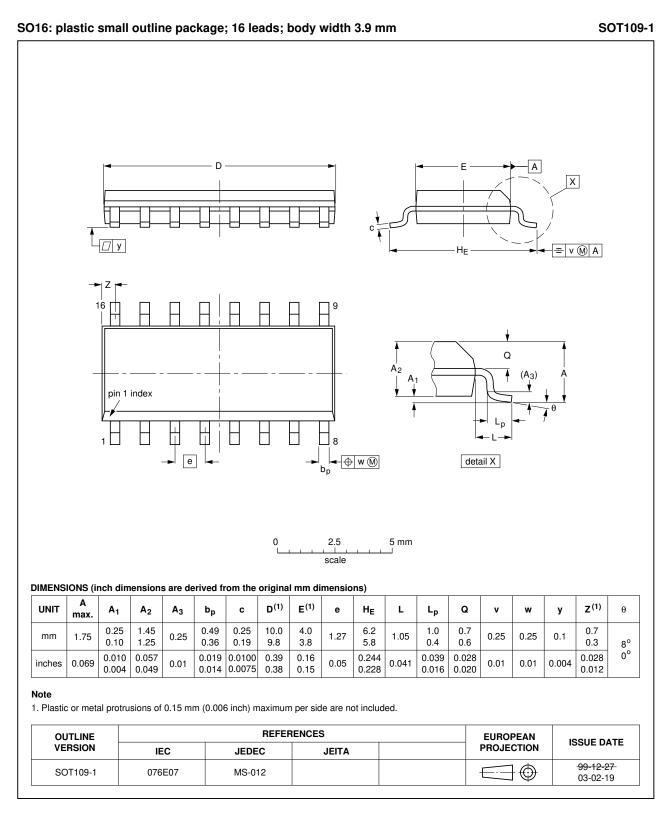


Fig 20. Package outline SOT109-1 (SO16)

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Power logic 8-bit shift register; open-drain outputs

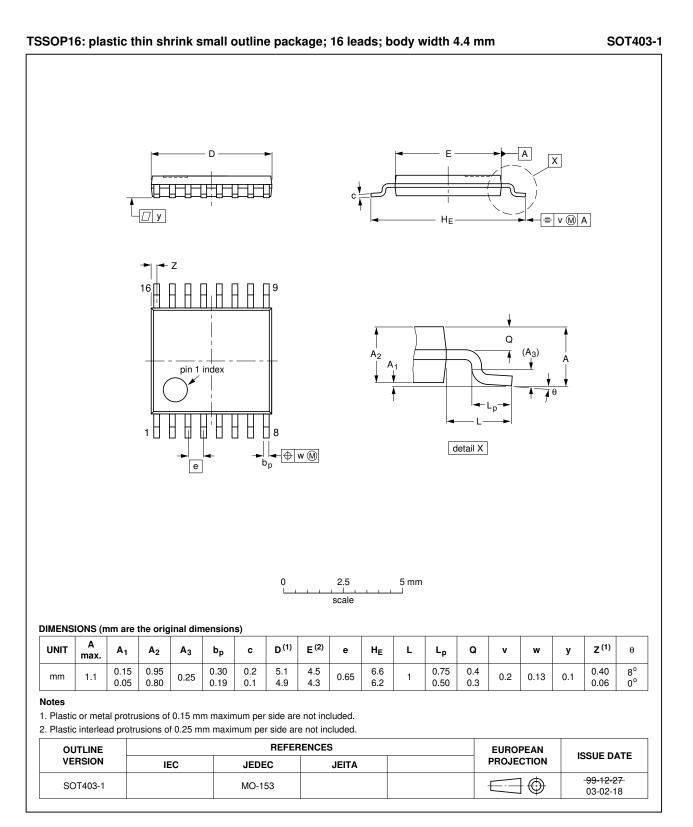
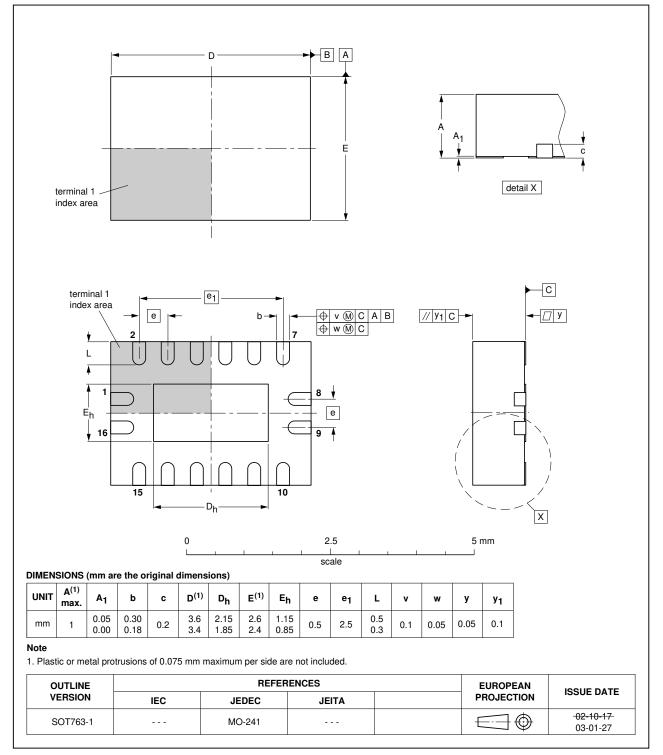


Fig 21. Package outline SOT403-1 (TSSOP16)

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Power logic 8-bit shift register; open-drain outputs



DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm SOT763-1

Fig 22. Package outline SOT763-1 (DHVQFN16)

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Power logic 8-bit shift register; open-drain outputs

12. Abbreviations

AcronymDescriptionCDMCharged Device ModelCMOSComplementary Metal Oxide SemiconductorDUTDevice Under TestEDNMOSExtended Drain Negative Metal Oxide SemiconductorESDElectroStatic DischargeHBMHuman Body ModelTTLTransistor-Transistor Logic	Table 10.	Abbreviations
CMOSComplementary Metal Oxide SemiconductorDUTDevice Under TestEDNMOSExtended Drain Negative Metal Oxide SemiconductorESDElectroStatic DischargeHBMHuman Body Model	Acronym	Description
DUTDevice Under TestEDNMOSExtended Drain Negative Metal Oxide SemiconductorESDElectroStatic DischargeHBMHuman Body Model	CDM	Charged Device Model
EDNMOSExtended Drain Negative Metal Oxide SemiconductorESDElectroStatic DischargeHBMHuman Body Model	CMOS	Complementary Metal Oxide Semiconductor
ESD ElectroStatic Discharge HBM Human Body Model	DUT	Device Under Test
HBM Human Body Model	EDNMOS	Extended Drain Negative Metal Oxide Semiconductor
	ESD	ElectroStatic Discharge
TTL Transistor-Transistor Logic	HBM	Human Body Model
	TTL	Transistor-Transistor Logic

13. Revision history

Table 11. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
NPIC6C595 v.1	20120820	Product data sheet	-	-	

Power logic 8-bit shift register; open-drain outputs

14. Legal information

14.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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